# Red, Green, Blue (RGB) SiPMs

Silicon photomultipliers (SiPMs) from First Sensor are innovative solid-state silicon detectors with single photon sensitivity. SiPMs are a valid alternative to photomultiplier tubes. The main benefits of these detectors are high gain, extremely good timing performance and low operating voltage. They are insensitive to magnetic field and have a high integration level. The detectors are optimized for red, green and blue (RGB) light detection.



#### Features

- RGB light detection from 350 to 900 nm (peak efficiency at 550 nm)
- Low noise
- Superior breakdown voltage uniformity
- Excellent temperature stability
- Detection of extremely faint light
- Very high gain (10°)
- Extremely good timing performance
- Insensitive to magnetic fields
- Not damaged by ambient light
- Small and compact
- Nickel free Chip Scale Package (CSP)

### Applications

- High energy physics
- Medical imaging
- Nuclear medicine
- Homeland security
- Analytical instruments

### Certificates

- RoHS compliant (2011/65/EU)

### Red, Green, Blue (RGB) SiPMs

### Absolute maximum ratings (1)

| Parameter   | Min. | Max.                 | Unit |
|---|------|----------------------|------|
| Operating temperature (T <sub>A</sub> )           | -25  | +40                  | °C   |
| Storage temperature (T <sub>s</sub> )             | -40  | +60                  | °C   |
| Lead temperature (solder) 5 s (T <sub>sol</sub> ) |      | +250                 | °C   |
| Voltage working range (MVW)                       |      | Breakdown voltage +4 | V    |

### Typical characteristics

| Parameter   | Product                                      |                      |                       |                       |  |  |
|---|--|----------------------|-----------------------|-----------------------|--|--|
|   | SiPM-RGB1S-SMD                               | SiPM-RGB1C-SMD       | SiPM-RGB3S-SMD        | SiPM-RGB4S-SMD        |  |  |
| Effective active area                             | (1×1) mm <sup>2</sup>                        | 1.13 mm <sup>2</sup> | (3×3) mm <sup>2</sup> | (4×4) mm <sup>2</sup> |  |  |
| Cell count  | 625  | 673                  | 5520                  | 9340                  |  |  |
| Cell size (pitch)                                 | 40 μm × 40 μm                                |                      |                       |                       |  |  |
| Cell fill-factor                                  | 60 %   |                      |                       |                       |  |  |
| Quenching resistance                              | 550 kΩ                                       |                      |                       |                       |  |  |
| Cell capacitance                                  | 90 fF  |                      |                       |                       |  |  |
| Recharge time constant                            | 50 ns  |                      |                       |                       |  |  |
| Spectral response range                           | 350 900 nm                                   |                      |                       |                       |  |  |
| Peak sensitivity wavelength                       | 550 nm                                       |                      |                       |                       |  |  |
| Photon detection efficiency <sup>(2)</sup>        | 32.5 %                                       |                      |                       |                       |  |  |
| Breakdown voltage (BV) <sup>(3)</sup>             | typ. 27 V, min. 25 V, max. 29 V              |                      |                       |                       |  |  |
| BV standard deviation <sup>(4)</sup>              | 50 mV  |                      |                       |                       |  |  |
| Recommended overvoltage range (OV) <sup>(5)</sup> | min: 2 V, max: 4 V                           |                      |                       |                       |  |  |
| Dark count rate <sup>(6)</sup>                    | <100 kHz/mm² @ 2 V OV, <200 kHz/mm² @ 4 V OV |                      |                       |                       |  |  |
| Gain <sup>(7)</sup>                               | 2.7×10 <sup>6</sup>                          |                      |                       |                       |  |  |
| Breakdown voltage temperature coefficient         | 27 mV/°C                                     |                      |                       |                       |  |  |
| Refractive index of epoxy resin <sup>(8)</sup>    | 1.5115 (@ 589 nm, 23 °C, uncured)            |                      |                       |                       |  |  |
| Spectral transmission of epoxy resin (8)          | >97% @ 1000 1600 nm ; >99% @ 400 1000 nm     |                      |                       |                       |  |  |

pectral transmission of epoxy resin

#### Specification notes

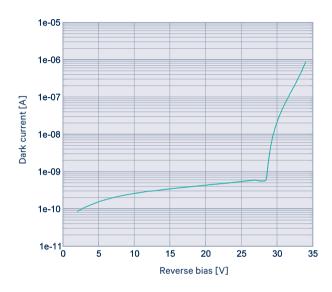
- (1) Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rated conditions for extended periods may affect device reliability.
- (2) Measured at peak sensitivity wavelength ( $\lambda = \lambda_{n}$ ) at +4 V overvoltage (not including afterpulse and crosstalk).
- (3) Refer to the data provided with each shipped product.

- (4) BV of SiPMs belonging to a same production lot are within 200 mV ( $\pm 2\sigma$ ) from mean BV value.
- (5) Operating voltage (SiPM bias) is BV+OV, to be applied in reverse mode, i.e. V<sub>AV</sub> <0 (see "Pins Function" section).
- (6) 0.5 p.e. threshold level at 20 °C (primary dark count rate; not including afterpulse).
- (7) Measured at 20 °C at +4 V overvoltage.
- (8) To be used as a guide only, not as a specification. Reported data is not guaranteed.

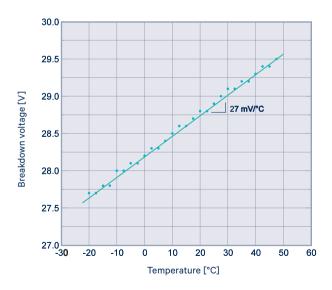
# Red, Green, Blue (RGB) SiPMs

### Device characteristics (9, 10)

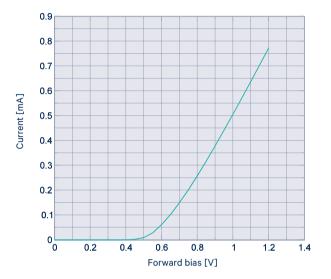
#### Typical reverse IV curve (SiPM-RGB1S-SMD)



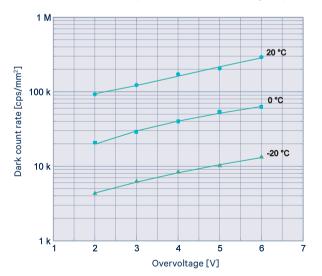
#### Breakdown voltage temperature dependence



#### Typical forward IV curve (SiPM-RGB1S-SMD)



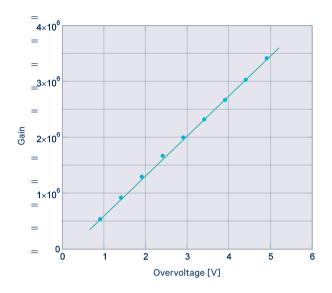
#### Dark count rate as fct of overvoltage and temperature (0.5 p.e. threshold level; primary dark count rate; not including afterpulse)



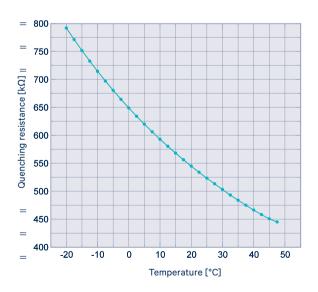
# Red, Green, Blue (RGB) SiPMs

### Device characteristics (cont.) <sup>(9, 10)</sup>

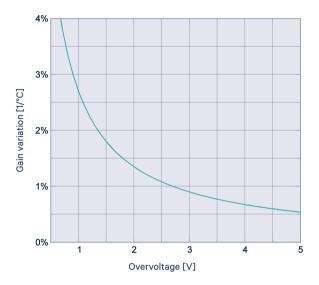
#### Gain as fct of overvoltage



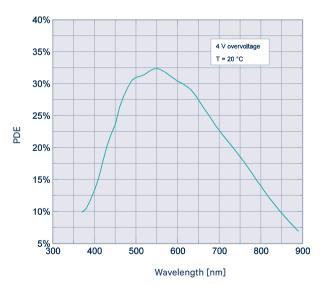
### Temperature dependence of poly-silicon quenching resistance



### Relative variation of gain with temperature as fct of overvoltage



### Photo detection efficiency (PDE) as fct of wavelength (crosstalk and afterpulse not included)

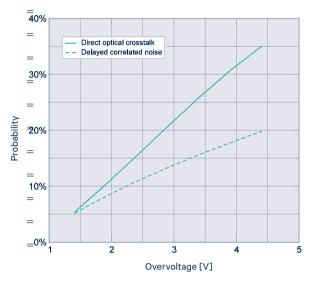


# Red, Green, Blue (RGB) SiPMs

### Device characteristics (cont.) <sup>(9, 10)</sup>

#### Correlated noise probability as fct of overvoltage

(delayed correlated noise includes delayed crosstalk and afterpulse)

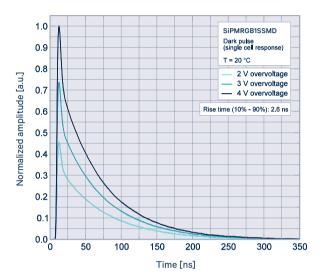


#### Specification notes

- (9) T<sub>4</sub> = 20 °C
- (10) Refer to the data accompanying each shipped product for more detailed information.

#### Pulse shape at different overvoltage

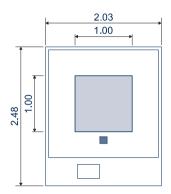
(recharge time constant is 50 ns)

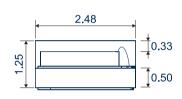


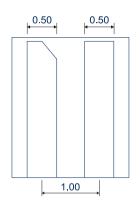
# Red, Green, Blue (RGB) SiPMs

### Physical dimensions

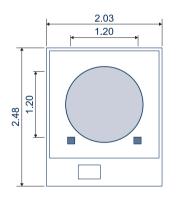
#### SiPM-RGB1S-SMD



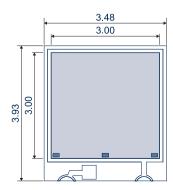




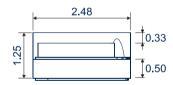
#### SiPM-RGB1C-SMD

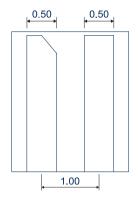


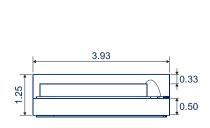
#### SiPM-RGB3S-SMD

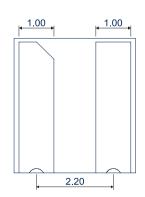


Material: Black FR4, transparent epoxy layer







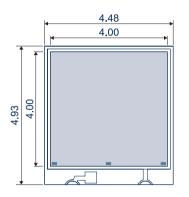


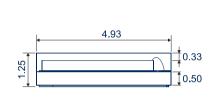
dimensions in mm, mechanical tolerance  $\pm 0.15$  mm unless otherwise noted

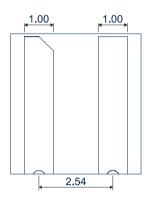
## Red, Green, Blue (RGB) SiPMs

### Physical dimensions (cont.)

#### SiPM-RGB4S-SMD



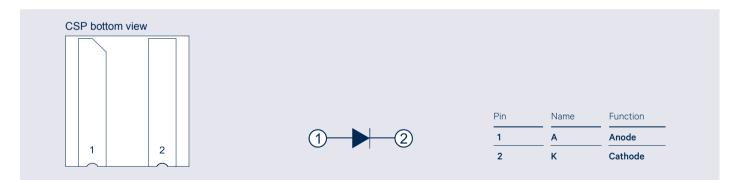




Material: Black FR4, transparent epoxy layer

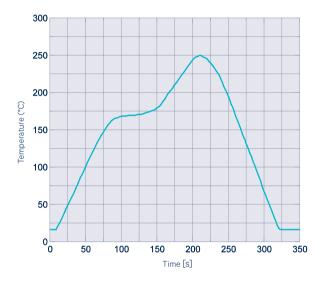
dimensions in mm, mechanical tolerance ±0.15 mm unless otherwise noted

### Electrical connection



## Red, Green, Blue (RGB) SiPMs

### Reflow soldering profile (11)



#### Specification notes

(11) The reflow soldering must be performed within 24 hours once the device has been removed from package and stored in a 25 °C and <60 % RH ambient conditions. The reflow soldering profile is recommended for Pb-free solder such as Tin-Silver-Copper (SAC). The peak temperature must not exceed 250 °C.

### Ordering information

| Order #  | Series | Range                  | Active area |                              | Housing                                 |
|----------|--------|------------------------|-------------|------------------------------|---|
| 50162901 | 162901 | RGB [Red, Green, Blue] | 1S          | (1x1) mm <sup>2</sup> square |   |
| 50162902 |        |                        | 1C          | Ø 1.2 mm circular            |   |
| 50162903 |        |                        | 3S          | (3x3) mm <sup>2</sup> square | -SMD [Plastic chip scale package (CSP)] |
| 50162904 |        |                        | 4S          | (4x4) mm <sup>2</sup> square |   |